Analog Multiplexers/Demultiplexers

The MC14051B, MC14052B, and MC14053B analog multiplexers are digitally—controlled analog switches. The MC14051B effectively implements an SP8T solid state switch, the MC14052B a DP4T, and the MC14053B a Triple SPDT. All three devices feature low ON impedance and very low OFF leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

Features

- Triple Diode Protection on Control Inputs
- Switch Function is Break Before Make
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Analog Voltage Range (V_{DD} V_{EE}) = 3.0 to 18 V Note: V_{EE} must be ≤ V_{SS}
- Linearized Transfer Characteristics
- Low-noise 12 nV/ $\sqrt{\text{Cycle}}$, f \geq 1.0 kHz Typical
- Pin-for-Pin Replacement for CD4051, CD4052, and CD4053
- For 4PDT Switch, See MC14551B
- For Lower R_{ON}, Use the HC4051, HC4052, or HC4053 High–Speed CMOS Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V _{DD}	DC Supply Voltage Range (Referenced to V_{EE} , $V_{SS} \ge V_{EE}$)	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient) (Referenced to V _{SS} for Control Inputs and V _{EE} for Switch I/O)	-0.5 to V _{DD} + 0.5	V
I _{in}	Input Current (DC or Transient) per Control Pin	+10	mA
I _{SW}	Switch Through Current	±25	mA
P _D	Power Dissipation per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C
 This device contains protection circuitry to guard against damage due to high
 static voltages or electric fields. However, precautions must be taken to avoid
 applications of any voltage higher than maximum rated voltages to this
 high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to

the range $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} , V_{EE} or V_{DD}). Unused outputs must be left open.



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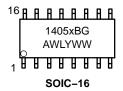
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TSSOP-16 DT SUFFIX CASE 948F

MARKING DIAGRAMS





TSSOP-16

x = 1, 2, or 3

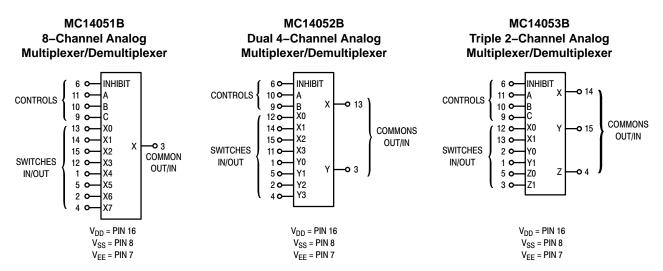
A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

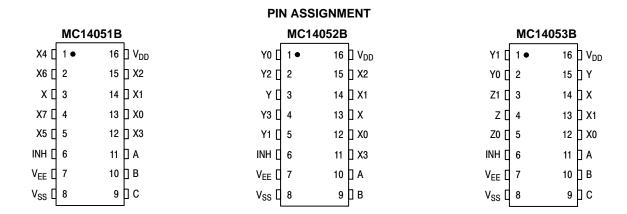
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.



Note: Control Inputs referenced to V_{SS}, Analog Inputs and Outputs reference to V_{EE}. V_{EE} must be ≤ V_{SS}.



ELECTRICAL CHARACTERISTICS

				−55°C 25°C		12	5°C				
Characteristic	Symbol	V _{DD}	Test Conditions	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
SUPPLY REQUIREMENTS	(Voltages I	Referer	nced to V _{EE})	l		I	ı	I		I	I
Power Supply Voltage Range	V _{DD}	-	$V_{DD} - 3.0 \ge V_{SS} \ge V_{EE}$	3.0	18	3.0	_	18	3.0	18	V
Quiescent Current Per Package	I _{DD}	5.0 10 15	$\label{eq:control Inputs: Vin = VSS or VDD,} V_{in} = V_{SS} \text{ or V}_{DD}, \\ Switch I/O: V_{EE} \leq V_{I/O} \leq V_{DD}, \text{ and } \Delta V_{switch} \leq 500 \text{ mV (Note 3)}$	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μΑ
Total Supply Current (Dynamic Plus Quiescent, Per Package	I _{D(AV)}	5.0 10 15	T _A = 25°C only (The channel component, (V _{in} – V _{out})/R _{on} , is not included.)		Typical	((0.07 μΑ/kHz (0.20 μΑ/kHz (0.36 μΑ/kHz) f + I _{DD})		μΑ
CONTROL INPUTS — INHII	BIT, A, B,	C (Volta	ages Referenced to V _{SS})								
Low-Level Input Voltage	V _{IL}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	V
High-Level Input Voltage	V _{IH}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	V
Input Leakage Current	I _{in}	15	$V_{in} = 0$ or V_{DD}	-	±0.1	-	±0.00001	±0.1	_	1.0	μΑ
Input Capacitance	C _{in}	-		-	-	-	5.0	7.5	-	-	pF
SWITCHES IN/OUT AND CO	OMMONS	OUT/II	N — X, Y, Z (Voltages Refere	nced to	V _{EE})						
Recommended Peak-to-Peak Voltage Into or Out of the Switch	V _{I/O}	1	Channel On or Off	0	V _{DD}	0	-	V _{DD}	0	V _{DD}	V _{PP}
Recommended Static or Dynamic Voltage Across the Switch (Note 3) (Figure 5)	ΔV_{switch}	-	Channel On	0	600	0	-	600	0	300	mV
Output Offset Voltage	V _{OO}	-	V _{in} = 0 V, No Load	-	-	-	10	-	-	-	μV
ON Resistance	R _{on}	5.0 10 15	$\begin{array}{l} \Delta V_{\text{switch}} \leq 500 \text{ mV} \\ \text{(Note 3) } V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}} \\ \text{(Control), and } V_{\text{in}} = \\ 0 \text{ to } V_{DD} \text{(Switch)} \end{array}$	- - -	800 400 220	- - -	250 120 80	1050 500 280	- - -	1200 520 300	Ω
AON Resistance Between Any Two Channels in the Same Package	ΔR_{on}	5.0 10 15		- - -	70 50 45	_ _ _	25 10 10	70 50 45	- - -	135 95 65	Ω
Off-Channel Leakage Current (Figure 10)	I _{off}	15	V _{in} = V _{IL} or V _{IH} (Control) Channel to Channel or Any One Channel	-	±100	-	±0.05	±100	-	±1000	nA
Capacitance, Switch I/O	C _{I/O}	_	Inhibit = V _{DD}	-	_	-	10	_	-	-	pF
Capacitance, Common O/I	C _{O/I}	ı	Inhibit = V _{DD} (MC14051B) (MC14052B) (MC14053B)	- - -	- - -	1 1 1	60 32 17	- - -		- - -	pF
Capacitance, Feedthrough (Channel Off)	C _{I/O}	- -	Pins Not Adjacent Pins Adjacent	_ _	-	_	0.15 0.47	-	_	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.

For voltage drops across the switch (ΔV_{switch}) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn, i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

$\textbf{ELECTRICAL CHARACTERISTICS} \text{ (Note 4) } (C_L = 50 \text{ pF, } T_A = 25^{\circ}\text{C) } \text{ ($V_{EE} \leq V_{SS}$ unless otherwise indicated)}$

Characteristic (Note 4) (C _L = 50	Symbol	V _{DD} – V _{EE} Vdc	Typ (Note 5) All Types	Max	Unit
Propagation Delay Times (Figure 6) Switch Input to Switch Output ($R_L = 1 \text{ k}\Omega$) MC14051	t _{PLH} , t _{PHL}				ns
t_{PLH} , t_{PHL} = (0.17 ns/pF) C_L + 26.5 ns t_{PLH} , t_{PHL} = (0.08 ns/pF) C_L + 11 ns t_{PLH} , t_{PHL} = (0.06 ns/pF) C_L + 9.0 ns		5.0 10 15	35 15 12	90 40 30	
MC14052 $t_{PLH}, t_{PHL} = (0.17 \text{ ns/pF}) \text{ C}_{L} + 21.5 \text{ ns} $ $t_{PLH}, t_{PHL} = (0.08 \text{ ns/pF}) \text{ C}_{L} + 8.0 \text{ ns} $ $t_{PLH}, t_{PHL} = (0.06 \text{ ns/pF}) \text{ C}_{L} + 7.0 \text{ ns} $		5.0 10 15	30 12 10	75 30 25	ns
MC14053 $t_{PLH}, t_{PHL} = (0.17 \text{ ns/pF}) \text{ C}_{L} + 16.5 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.08 \text{ ns/pF}) \text{ C}_{L} + 4.0 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.06 \text{ ns/pF}) \text{ C}_{L} + 3.0 \text{ ns}$		5.0 10 15	25 8.0 6.0	65 20 15	ns
Inhibit to Output ($R_L = 10 \text{ k}\Omega$, $V_{EE} = V_{SS}$) Output "1" or "0" to High Impedance, or High Impedance to "1" or "0" Level	t _{PHZ} , t _{PLZ} , t _{PZH} , t _{PZL}				ns
MC14051B		5.0 10 15	350 170 140	700 340 280	
MC14052B		5.0 10 15	300 155 125	600 310 250	ns
MC14053B		5.0 10 15	275 140 110	550 280 220	ns
Control Input to Output (R _L = 1 k Ω , V _{EE} = V _{SS}) MC14051B	t _{PLH} , t _{PHL}	5.0 10 15	360 160 120	720 320 240	ns
MC14052B		5.0 10 15	325 130 90	650 260 180	ns
MC14053B		5.0 10 15	300 120 80	600 240 160	ns
Second Harmonic Distortion $(R_L = 10 K\Omega, f = 1 \text{ kHz}) \text{ V}_{in} = 5 \text{ V}_{PP}$	-	10	0.07	_	%
Bandwidth (Figure 7) $ (R_L = 50 \ \Omega, \ V_{in} = 1/2 \ (V_{DD} - V_{EE}) \ p-p, \ C_L = 50 pF \\ 20 \ Log \ (V_{out}/V_{in}) = -3 \ dB) $	BW	10	17	-	MHz
Off Channel Feedthrough Attenuation (Figure 7) $R_L = 1 \text{K}\Omega, \text{V}_{\text{in}} = 1/2 \text{ (V}_{\text{DD}} - \text{V}_{\text{EE}}) \text{ p-p} \\ f_{\text{in}} = 4.5 \text{ MHz} - \text{MC}14051B \\ f_{\text{in}} = 30 \text{ MHz} - \text{MC}14052B \\ f_{\text{in}} = 55 \text{ MHz} - \text{MC}14053B \\ \end{cases}$	-	10	-50	-	dB
Channel Separation (Figure 8) $ (R_L = 1 \text{ k}\Omega, V_{in} = 1/2 \text{ (V}_{DD}V_{EE}) \text{ pp}, \\ f_{in} = 3.0 \text{ MHz} $	-	10	- 50	-	dB
Crosstalk, Control Input to Common O/I (Figure 9) $ (R_1 = 1 \text{ k}\Omega, R_L = 10 \text{ k}\Omega \\ \text{Control } t_{TLH} = t_{THL} = 20 \text{ ns, Inhibit} = V_{SS}) $	-	10	75	-	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The formulas given are for the typical characteristics only at 25°C.

5. Data labelled "Typ" is not lo be used for design purposes but In intended as an indication of the IC's potential performance.

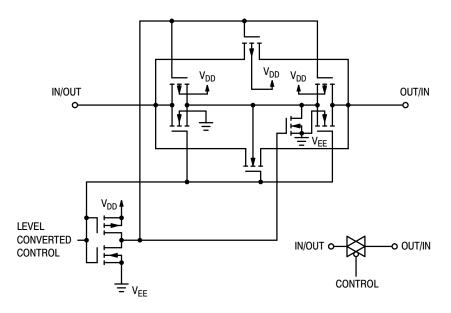


Figure 1. Switch Circuit Schematic

TRUTH TABLE

Cont	rol In	puts	5						
	Select			ON Switches					
Inhibit	C*	В	Α	MC14051B	MC14052B		MC	1405	3B
0	0	0	0	X0	Y0	X0	Z0	Y0	X0
0	0	0	1	X1	Y1	X1	Z0	Y0	X1
0	0	1	0	X2	Y2	X2	Z0	Y1	X0
0	0	1	1	Х3	Y3	Х3	Z0	Y1	X1
0	1	0	0	X4			Z1	Y0	X0
0	1	0	1	X5			Z1	Y0	X1
0	1	1	0	X6			Z1	Y1	X0
0	1	1	1	X7			Z1	Y1	X1
1	Х	Х	Х	None None None					

*Not applicable for MC14052

x = Don't Care

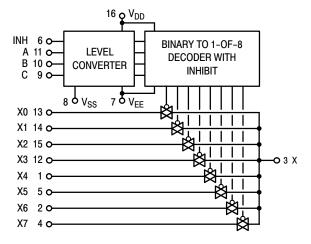


Figure 2. MC14051B Functional Diagram

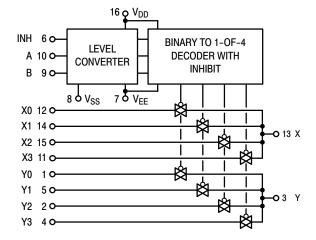


Figure 3. MC14052B Functional Diagram

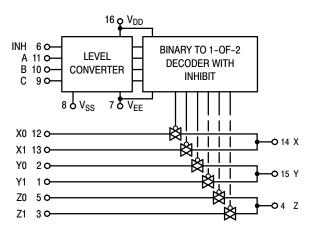


Figure 4. MC14053B Functional Diagram

TEST CIRCUITS

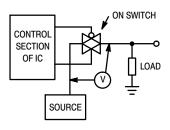


Figure 5. ΔV Across Switch

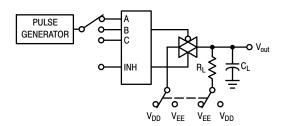


Figure 6. Propagation Delay Times, Control and Inhibit to Output

A, B, and C inputs used to turn ON or OFF the switch under test.

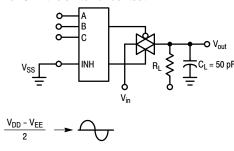


Figure 7. Bandwidth and Off-Channel Feedthrough Attenuation

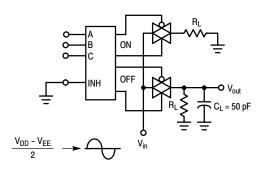


Figure 8. Channel Separation (Adjacent Channels Used For Setup)

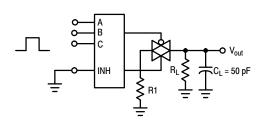


Figure 9. Crosstalk, Control Input to Common O/I

NOTE: See also Figures 7 and 8 in the MC14016B data sheet.

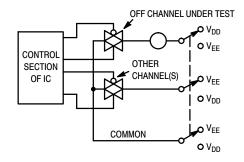


Figure 10. Off Channel Leakage

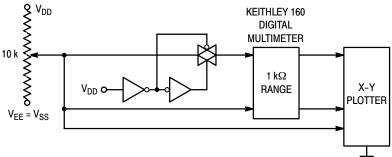
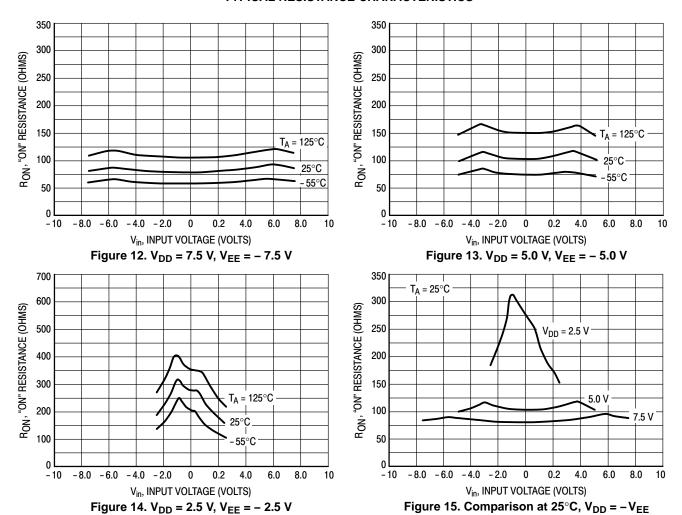


Figure 11. Channel Resistance (R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS



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APPLICATIONS INFORMATION

Figure A illustrates use of the on–chip level converter detailed in Figures 2, 3, and 4. The 0–to–5 V Digital Control signal is used to directly control a 9 V_{p-p} analog signal.

The digital control logic levels are determined by V_{DD} and V_{SS} . The V_{DD} voltage is the logic high voltage; the V_{SS} voltage is logic low. For the example, $V_{DD} = +5 \ V = logic$ high at the control inputs; $V_{SS} = GND = 0 \ V = logic$ low.

The maximum analog signal level is determined by V_{DD} and V_{EE} . The V_{DD} voltage determines the maximum recommended peak above V_{SS} . The V_{EE} voltage determines the maximum swing below V_{SS} . For the example, $V_{DD} - V_{SS} = 5$ V maximum swing above V_{SS} ; $V_{SS} - V_{EE} = 5$ V maximum swing below V_{SS} . The example shows a ± 4.5 V signal which allows a 1/2 volt margin at each

peak. If voltage transients above V_{DD} and/or below V_{EE} are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The *absolute* maximum potential difference between V_{DD} and V_{EE} is 18.0 V. Most parameters are specified up to 15 V which is the *recommended* maximum difference between V_{DD} and V_{EE} .

Balanced supplies are not required. However, V_{SS} must be greater than or equal to V_{EE} . For example, $V_{DD} = +10 \text{ V}$, $V_{SS} = +5 \text{ V}$, and $V_{EE} - 3 \text{ V}$ is acceptable. See the Table below.

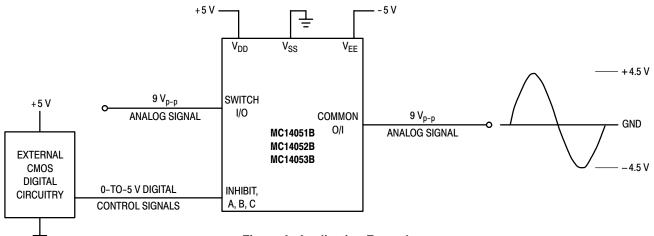


Figure A. Application Example

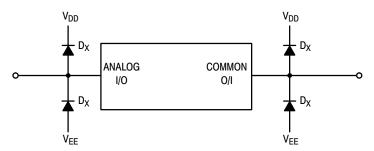


Figure B. External Germanium or Schottky Clipping Diodes

POSSIBLE SUPPLY CONNECTIONS

V _{DD} In Volts	V _{SS} In Volts	V _{EE} In Volts	Control Inputs Logic High/Logic Low In Volts	Maximum Analog Signal Range In Volts
+8	0	-8	+8/0	$+8 \text{ to } -8 = 16 \text{ V}_{p-p}$
+5	0	-12	+5/0	$+5 \text{ to } -12 = 17 \text{ V}_{p-p}$
+5	0	0	+5/0	$+5 \text{ to } 0 = 5 \text{ V}_{p-p}$
+5	0	-5	+5/0	$+5 \text{ to } -5 = 10 \text{ V}_{p-p}$
+10	+5	- 5	+10/ +5	$+10 \text{ to } -5 = 15 \text{ V}_{p-p}$

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14051BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14051BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14051BDR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
NLV14051BDR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC14051BDTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV14051BDTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
MC14052BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14052BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14052BDR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
NLV14052BDR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC14052BDTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV14052BDTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
MC14053BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14053BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14053BDR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
NLV14053BDR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC14053BDTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV14053BDTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006

- NOTES:

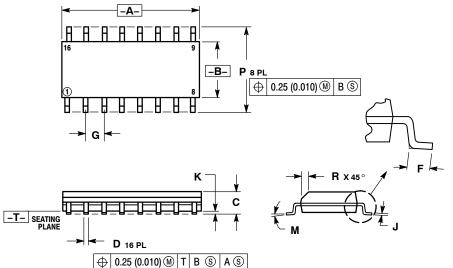
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD DESCRIPTION AND BEAUTION AND BEAUTION AND BEAUTION AND BEAUTION AND BEAUTI

- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



2. 3. 4. 5. 6. 7. 8. 9.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE CATHODE ANODE NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3	2. 3. 4. 5. 6. 7. 8. 9.	COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3	1	
12.	EMITTER BASE		CATHODE CATHODE	12.		12.		BECOM	MMENDED
13. 14.	COLLECTOR	13.	NO CONNECTION	13.	COLLECTOR, #4 BASE, #4	13. 14.	BASE, #2 EMITTER, #2		
15.	EMITTER		ANODE		EMITTER, #4	15.	BASE, #1	SOLDERING	G FOOTPRINT*
16.			CATHODE		COLLECTOR, #4		EMITTER, #1		8X
	002220.0		0,111002		0022201011,#1			L	6.40
STYLE 5:		STYLE 6:		STYLE 7:					0.40
	DRAIN, DYE #1		CATHODE		SOURCE N-CH				16X 1.12 <
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)			
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU			1	16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	•,	1	<i>'</i> ==	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	_		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X		
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58 ^{_1}		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH				<u> </u>
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		-		_
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3		ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.		13.	GATE N-CH	_			
14.	SOURCE, #2		ANODE	14.	COMMON DRAIN (OUTPU				. ☐ ↓ PITCH
15.	GATE, #1		ANODE	15.	COMMON DRAIN (OUTPU	1)			
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 + +

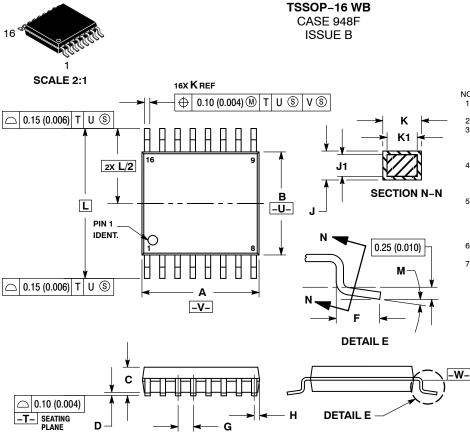
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DATE 19 OCT 2006

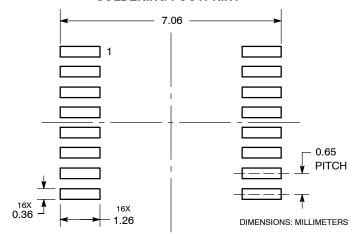


NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
NA.	00	00	0.0	0	

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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